



TPM401

NPN RF POWER TRANSISTOR

DESCRIPTION:

The **TPM401** is a Common Emitter Device Designed for Class A and AB Amplifier Applications up to 1.0 GHz.

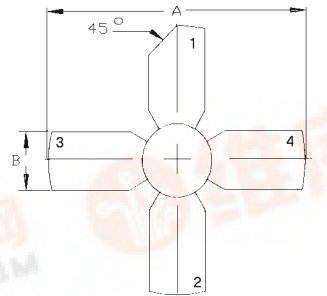
FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

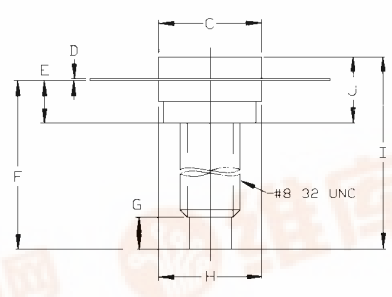
MAXIMUM RATINGS

I_C	400 mA
V_{CB0}	40 V
P_{DISS}	8.75 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	20 °C/W

PACKAGE STYLE 280 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.1010/25.65	.1055/26.80
B	.0220/5.59	.0230/5.84
C	.0270/6.86	.0285/7.24
D	.0003/0.08	.0007/0.18
E	.0117/2.97	.0137/3.48
F	.05/2/14.53	
G	.0130/3.30	
H	.0275/6.99	.0285/7.24
I	.640/16.26	
J	.0175/4.45	.021/75.51



1 = Collector 2 = Base
3 & 4 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 1.0 mA	40			V
BV_{CEO}	I _C = 1.0 mA	28			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	20		120	---
C_{OB}	V _{CB} = 28 f = 1.0 MHz			5.0	pF
P_G	V _{CE} = 24 V I _C = 200 mA f = 400 MHz P _{OUT} = 1.0 W	13	15		dB
P_{1dB}	V _{CE} = 24 V I _C = 200 mA f = 400 MHz		2.0		W

